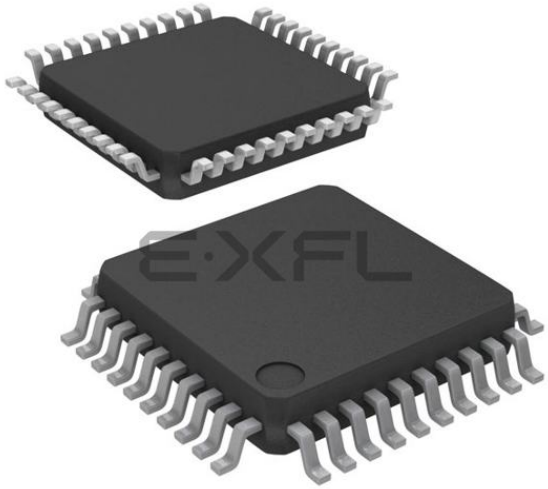
Renesas Electronics America Inc - R5F104BCDFP#X0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 8x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104bcdfp-x0

[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		44-pin R5F104Fx (x = F to H, J)	48-pin R5F104Gx (x = F to H, J)	52-pin R5F104Jx (x = F to H, J)	64-pin R5F104Lx (x = F to H, J)
Code flash memory (KB)		96 to 256	96 to 256	96 to 256	96 to 256
Data flash memory (KB)		8	8	8	8
RAM (KB)		12 to 24 Note	12 to 24 Note	12 to 24 Note	12 to 24 Note
Address space		1 MB			
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V			
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f_{IH} = 32 MHz operation)			
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)			
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)			
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.			
I/O port	Total	40	44	48	58
	CMOS I/O	31	34	38	48
	CMOS input	5	5	5	5
	CMOS output	—	1	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4	4	4
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 14 channels PWM outputs: 9 channels			
	RTC output	1 • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)			

(**Note** is listed on the next page.)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(3/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EV_{DD0}		EV_{DD0}	V
	V_{IH2}	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV_{DD0} ≤ 5.5 V	2.2		EV_{DD0}	V
			TTL input buffer 3.3 V ≤ EV_{DD0} < 4.0 V	2.0		EV_{DD0}	V
			TTL input buffer 1.6 V ≤ EV_{DD0} < 3.3 V	1.5		EV_{DD0}	V
	V_{IH3}	P20 to P27, P150 to P156		0.7 V_{DD}		V_{DD}	V
	V_{IH4}	P60 to P63		0.7 EV_{DD0}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EV_{DD0}	V
	V_{IL2}	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EV_{DD0} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ EV_{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EV_{DD0} < 3.3 V	0		0.32	V
	V_{IL3}	P20 to P27, P150 to P156		0		0.3 V_{DD}	V
	V_{IL4}	P60 to P63		0		0.3 EV_{DD0}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.

Note 8. Current flowing during programming of the data flash.

Note 9. Current flowing during self-programming.

Note 10. For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode** in the RL78/G14 User's Manual.

Note 11. Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{DAC} when the D/A converter operates in an operation mode or the HALT mode.

Note 12. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{CMP} when the comparator circuit is in operation.

Note 13. A comparator and D/A converter are provided in products with 96 KB or more code flash memory.

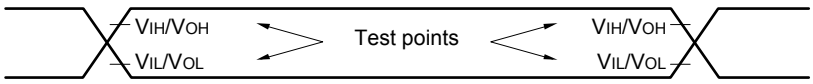
Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

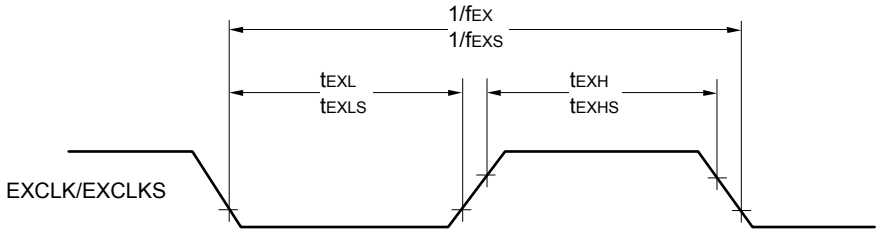
Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

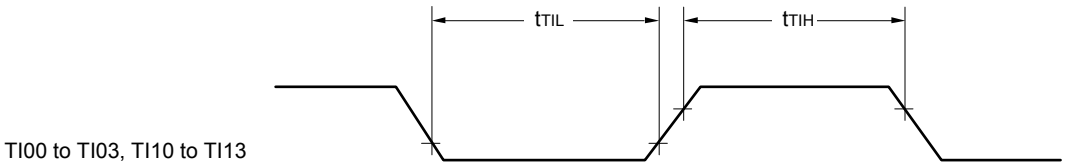
AC Timing Test Points

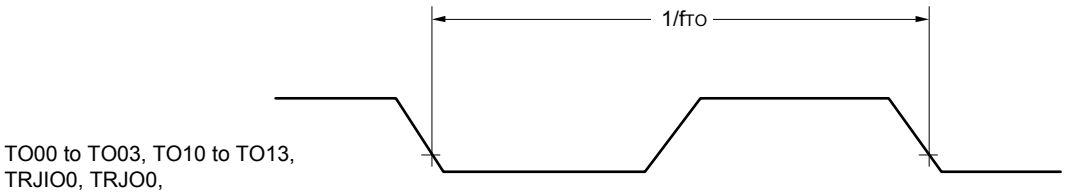


External System Clock Timing



TI/TO Timing





(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

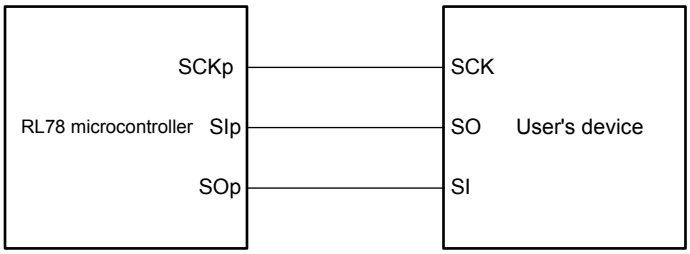
(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
$\overline{SSI00}$ setup time	t_{SSIK}	DAPmn = 0	2.7 V ≤ EV_{DD0} ≤ 5.5 V	120		120		120		ns
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	200		200		200		ns
			1.7 V ≤ EV_{DD0} ≤ 5.5 V	400		400		400		ns
			1.6 V ≤ EV_{DD0} ≤ 5.5 V	—		400		400		ns
		DAPmn = 1	2.7 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 120		1/f_{MCK} + 120		1/f_{MCK} + 120		ns
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 200		1/f_{MCK} + 200		1/f_{MCK} + 200		ns
			1.7 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 400		1/f_{MCK} + 400		1/f_{MCK} + 400		ns
			1.6 V ≤ EV_{DD0} ≤ 5.5 V	—		1/f_{MCK} + 400		1/f_{MCK} + 400		ns
$\overline{SSI00}$ hold time	t_{KSSI}	DAPmn = 0	2.7 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 120		1/f_{MCK} + 120		1/f_{MCK} + 120		ns
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 200		1/f_{MCK} + 200		1/f_{MCK} + 200		ns
			1.7 V ≤ EV_{DD0} ≤ 5.5 V	1/f_{MCK} + 400		1/f_{MCK} + 400		1/f_{MCK} + 400		ns
			1.6 V ≤ EV_{DD0} ≤ 5.5 V	—		1/f_{MCK} + 400		1/f_{MCK} + 400		ns
		DAPmn = 1	2.7 V ≤ EV_{DD0} ≤ 5.5 V	120		120		120		ns
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	200		200		200		ns
			1.7 V ≤ EV_{DD0} ≤ 5.5 V	400		400		400		ns
			1.6 V ≤ EV_{DD0} ≤ 5.5 V	—		400		400		ns

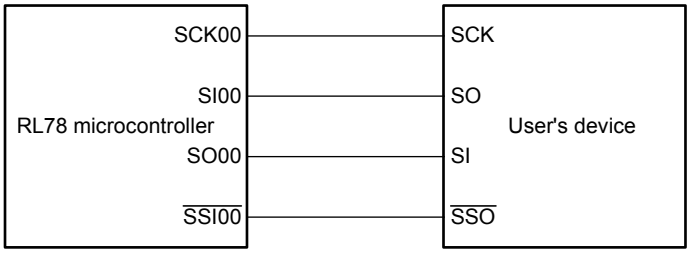
Caution **Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).**

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)



CSI mode connection diagram (during communication at same potential)
(Slave Transmission of slave select input function (CSI00))



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 3		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		1150		ns
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		1150		ns
			1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 12		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 18		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns

Note Use it with $EV_{DD0} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	355	0	355	0	355	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	0	405	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

Note 2. Use it with EV_{DD0} ≥ V_b.

Note 3. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

(2) Interrupt & Reset Mode

(T_A = -40 to +85°C, $V_{PDR} \le V_{DD} \le$ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Voltage detection threshold	V_{LVDA0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 0, 0, falling reset voltage		1.60	1.63	1.66	V
	V_{LVDA1}	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
			Falling interrupt voltage	1.70	1.73	1.77	V
	V_{LVDA2}	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
			Falling interrupt voltage	1.80	1.84	1.87	V
	V_{LVDA3}	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDB0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 0, 1, falling reset voltage		1.80	1.84	1.87	V
	V_{LVDB1}	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVDB2}	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVDB3}	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVDC0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 0, falling reset voltage		2.40	2.45	2.50	V
	V_{LVDC1}	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVDC2}	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVDC3}	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	V_{LVDD0}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 1, falling reset voltage		2.70	2.75	2.81	V
	V_{LVDD1}	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDD2}	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	V_{LVDD3}	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

2.6.7 Power supply voltage rising slope characteristics

(T_A = -40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

3.3 DC Characteristics

3.3.1 Pin characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	2.4 V ≤ EV_{DD0} ≤ 5.5 V			-3.0 Note 2	mA
		Total of P00 to P04, P40 to P47, P102, P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			-30.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			-10.0	mA
			2.4 V ≤ EV_{DD0} < 2.7 V			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			-30.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			-19.0	mA
			2.4 V ≤ EV_{DD0} < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.4 V ≤ EV_{DD0} ≤ 5.5 V			-60.0	mA
	I_{OH2}	Per pin for P20 to P27, P150 to P156	2.4 V ≤ V_{DD} ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	2.4 V ≤ V_{DD} ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(4/5)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = -3.0 mA	EV_{DD0} - 0.7			V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = -2.0 mA	EV_{DD0} - 0.6			V
			2.4 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = -1.5 mA	EV_{DD0} - 0.5			V
	V_{OH2}	P20 to P27, P150 to P156	2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = -100 μA	V_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			2.4 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
	V_{OL2}	P20 to P27, P150 to P156	2.4 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60 to P63	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			2.4 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V

Caution **P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.**

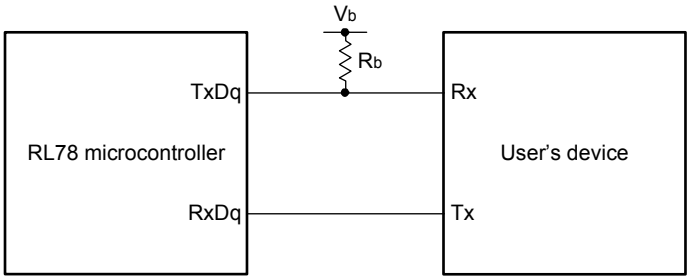
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(5/5)**

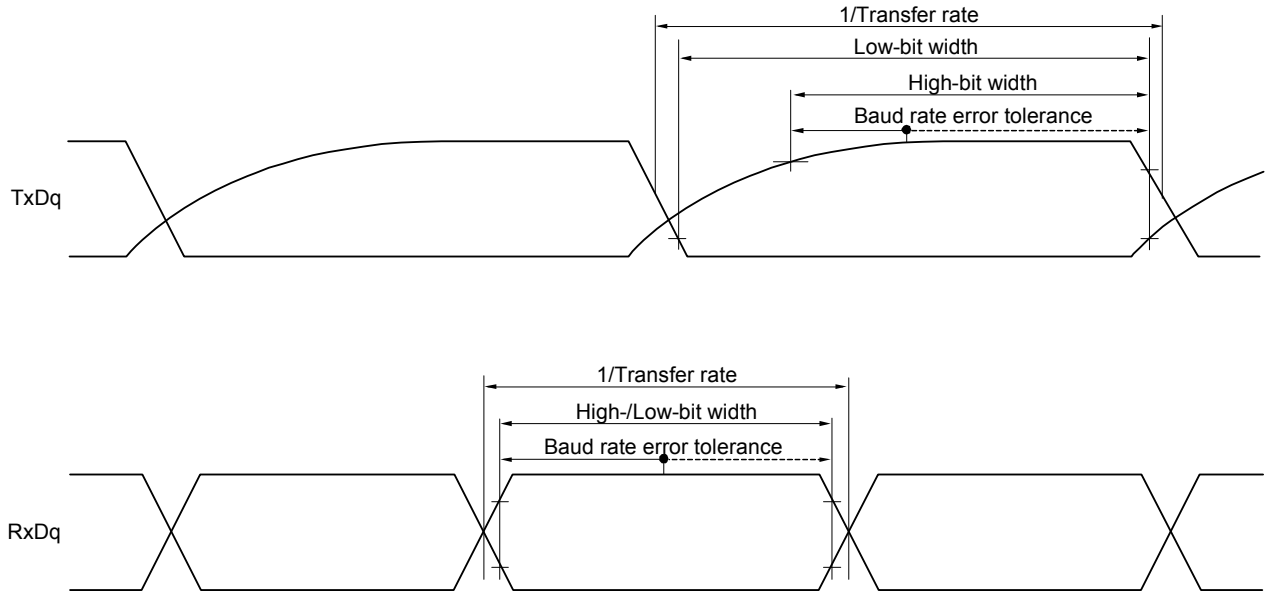
Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V_I = EV_{DD0}				1	μA
	I_{LIH2}	P20 to P27, P137, P150 to P156, $\overline{RESET}$	V_I = V_{DD}				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V_I = V_{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	I_{LIL1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V_I = EV_{SS0}				-1	μA
	I_{LIL2}	P20 to P27, P137, P150 to P156, $\overline{RESET}$	V_I = V_{SS}				-1	μA
	I_{LIL3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	V_I = V_{SS}	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	R_U	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V_I = EV_{SS0}, In input port		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. R_b[Ω]: Communication line (TxDq) pull-up resistance,
C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

3.6.6 LVD circuit characteristics

(1) Reset Mode and Interrupt Mode

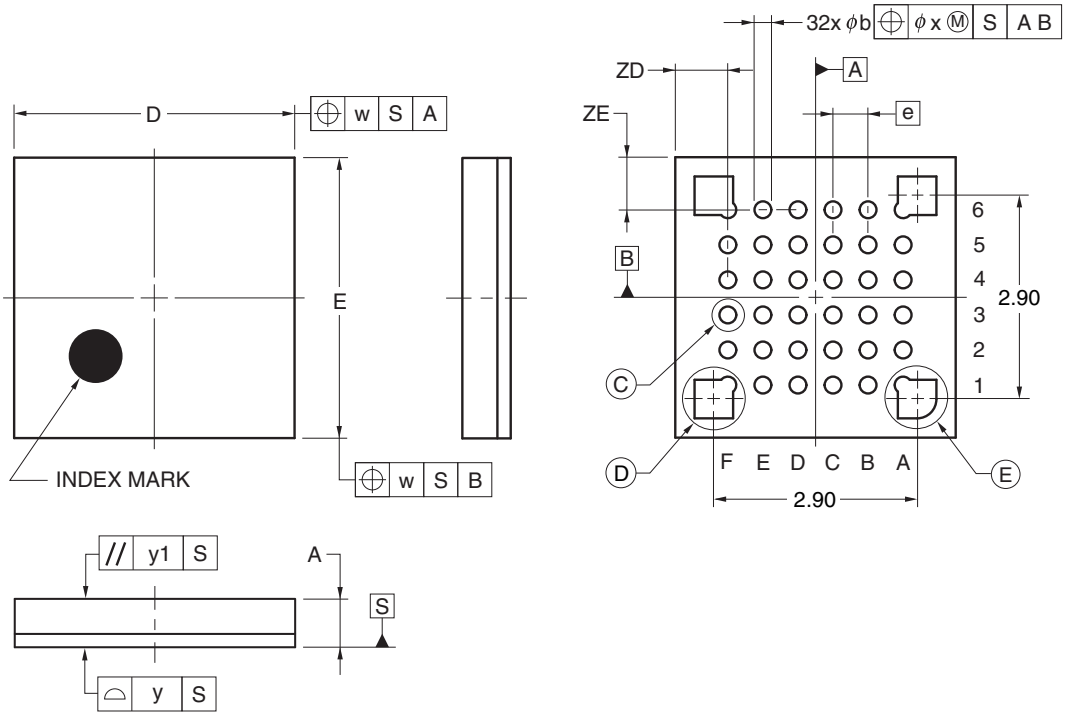
(T_A = -40 to +105°C, $V_{PDR} \leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

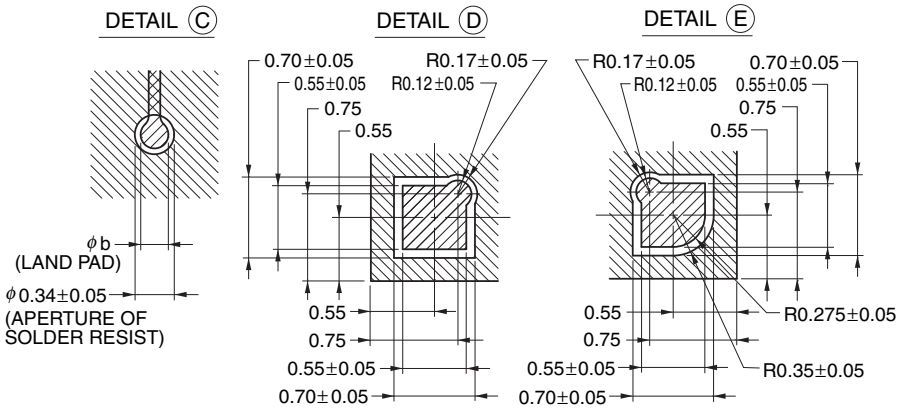
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection threshold	Supply voltage level	V_{LVD0}	Rising edge	3.90	4.06	4.22	V
			Falling edge	3.83	3.98	4.13	V
		V_{LVD1}	Rising edge	3.60	3.75	3.90	V
			Falling edge	3.53	3.67	3.81	V
		V_{LVD2}	Rising edge	3.01	3.13	3.25	V
			Falling edge	2.94	3.06	3.18	V
		V_{LVD3}	Rising edge	2.90	3.02	3.14	V
			Falling edge	2.85	2.96	3.07	V
		V_{LVD4}	Rising edge	2.81	2.92	3.03	V
			Falling edge	2.75	2.86	2.97	V
		V_{LVD5}	Rising edge	2.70	2.81	2.92	V
			Falling edge	2.64	2.75	2.86	V
		V_{LVD6}	Rising edge	2.61	2.71	2.81	V
			Falling edge	2.55	2.65	2.75	V
		V_{LVD7}	Rising edge	2.51	2.61	2.71	V
			Falling edge	2.45	2.55	2.65	V
Minimum pulse width		t_{LW}		300			µs
Detection delay time						300	µs

4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA
R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



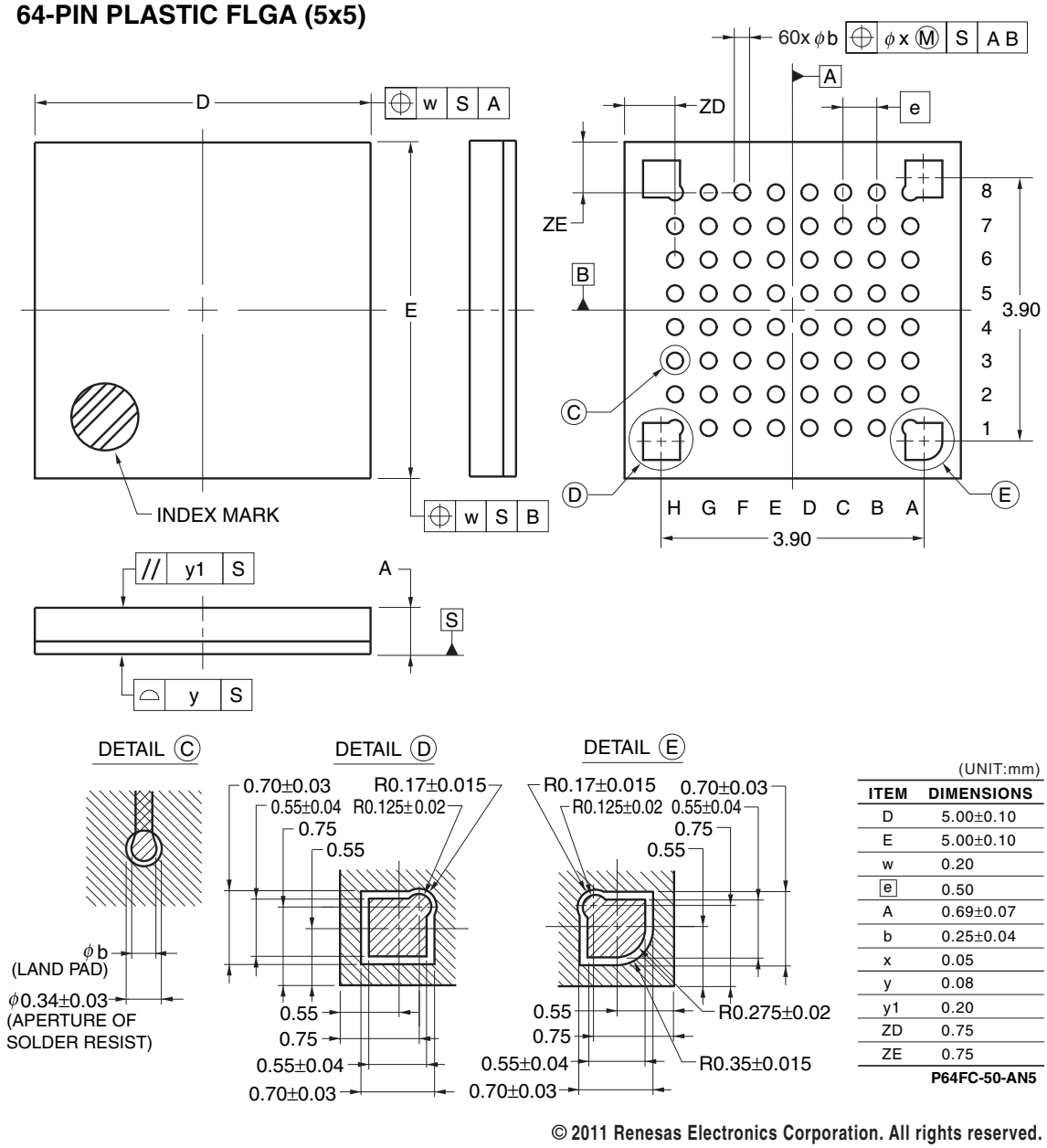


(UNIT:mm)

ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.24±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.75
ZE	0.75

R5F104LCALA, R5F104LDALA, R5F104LEALA, R5F104LFALA, R5F104LGALA, R5F104LHALA, R5F104LJALA
R5F104LKALA, R5F104LLALA
R5F104LCGLA,R5F104LDGLA, R5F104LEGLA, R5F104LFGLA, R5F104LGGLA, R5F104LHGLA, R5F104LJGLA
R5F104LKGLA, R5F104LLGLA

64-PIN PLASTIC FLGA (5x5)



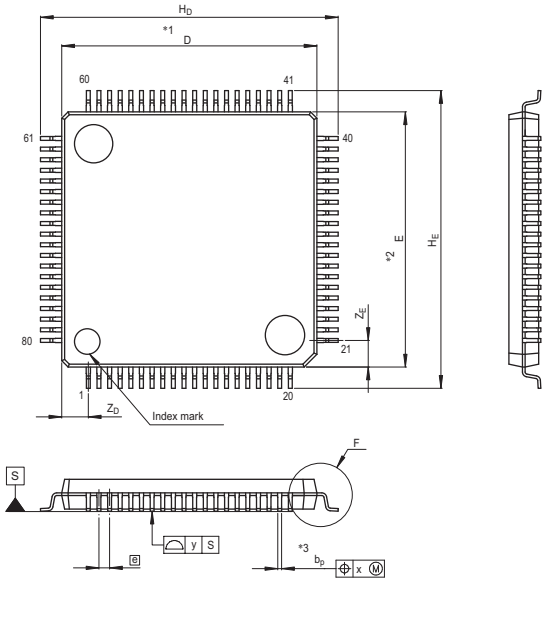
(UNIT:mm)

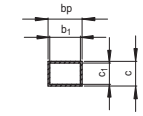
ITEM	DIMENSIONS
D	5.00±0.10
E	5.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.25±0.04
x	0.05
y	0.08
y1	0.20
ZD	0.75
ZE	0.75

P64FC-50-AN5

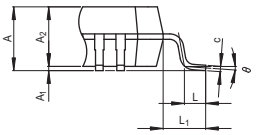
R5F104MKAFB, R5F104MLAFB
R5F104MKGFB, R5F104MLGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP80-12x12-0.50	PLQP0080KB-A	80P6Q-A	0.5g





Terminal cross section



Detail F

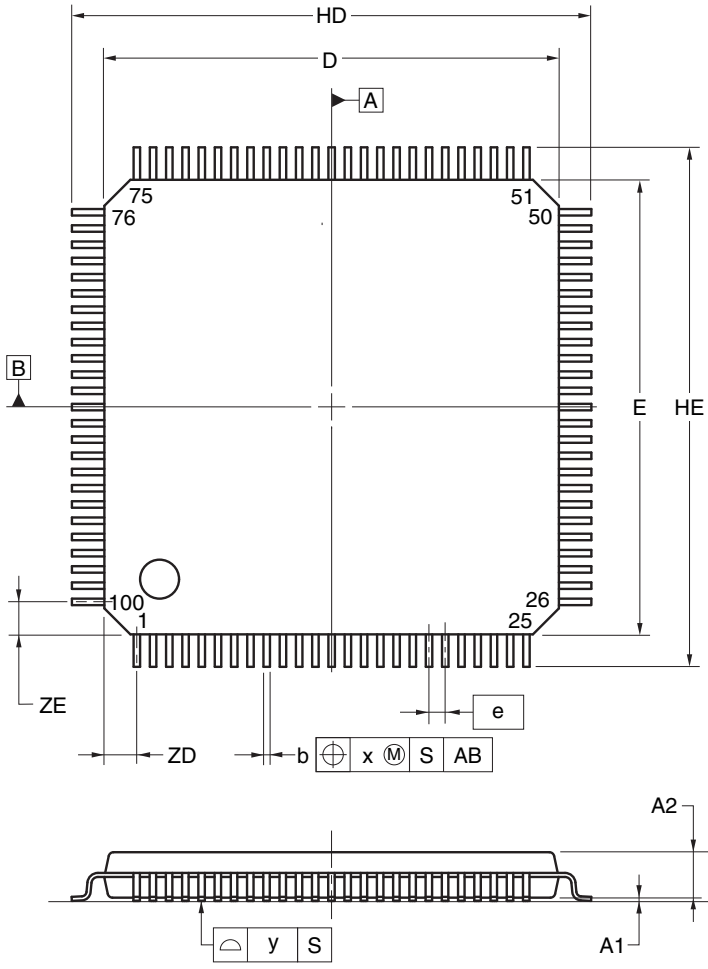
NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	11.9	12.0	12.1
E	11.9	12.0	12.1
A_2	—	1.4	—
H_D	13.8	14.0	14.2
H_E	13.8	14.0	14.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	10°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.25	—
Z_E	—	1.25	—
L	0.3	0.5	0.7
L_1	—	1.0	—

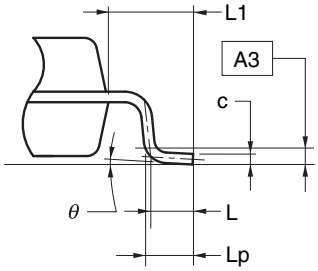
4.10 100-pin products

R5F104PFAFB, R5F104PGAFB, R5F104PHAFB, R5F104PJAFB
R5F104PFDFB, R5F104PGDFB, R5F104PHDFB, R5F104PJDFB
R5F104PFGFB, R5F104PGGFB, R5F104PHGFB, R5F104PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	14.00±0.20
E	14.00±0.20
HD	16.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.50
x	0.08
y	0.08
ZD	1.00
ZE	1.00

REVISION HISTORY	RL78/G14 Datasheet

Rev.	Date	Description	
		Page	Summary
0.01	Feb 10, 2011	—	First Edition issued
0.02	May 01, 2011	1 to 2	1.1 Features revised
		3	1.2 Ordering Information revised
		4 to 13	1.3 Pin Configuration (Top View) revised
		14	1.4 Pin Identification revised
		15 to 17	1.5.1 30-pin products to 1.5.3 36-pin products revised
		23 to 26	1.6 Outline of Functions revised
0.03	Jul 28, 2011	1	1.1 Features revised
1.00	Feb 21, 2012	1 to 40	1. OUTLINE revised
		41 to 97	2. ELECTRICAL SPECIFICATIONS added
2.00	Oct 25, 2013	1	Modification of 1.1 Features
		3 to 8	Modification of 1.2 Ordering Information
		9 to 22	Modification of package type in 1.3 Pin Configuration (Top View)
		34 to 43	Modification of description of subsystem clock in 1.6 Outline of Functions
		34 to 43	Modification of description of timer output in 1.6 Outline of Functions
		34 to 43	Modification of error of data transfer controller in 1.6 Outline of Functions
		34 to 43	Modification of error of event link controller in 1.6 Outline of Functions
		45, 46	Modification of description of Tables in 2.1 Absolute Maximum Ratings
		47	Modification of Tables, notes, cautions, and remarks in 2.2 Oscillator Characteristics
		48	Modification of error of conditions of high level input voltage in 2.3.1 Pin characteristics
		49	Modification of error of conditions of low level output voltage in 2.3.1 Pin characteristics
		53 to 62	Modification of Notes and Remarks in 2.3.2 Supply current characteristics
		65, 66	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		67 to 69	Addition of AC Timing Test Points
		70 to 97	Addition of LS mode and LV mode characteristics in 2.5.1 Serial array unit
		98 to 101	Addition of LS mode and LV mode characteristics in 2.5.2 Serial interface IICA
		102 to 105	Addition of characteristics about conversion of internal reference voltage and temperature sensor in 2.6.1 A/D converter characteristics
		107	Addition of characteristic in 2.6.4 Comparator
		107	Deletion of detection delay in 2.6.5 POR circuit characteristics
		109	Modification of 2.6.7 Power supply voltage rising slope characteristics
		110	Modification of 2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics
		110	Addition of characteristic in 2.8 Flash Memory Programming Characteristics
		111	Addition of description in 2.10 Timing for Switching Flash Memory Programming Modes

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